Silicon NPN Power Transistors 2SC2688

DESCRIPTION

·With TO-126 package
·High breakdown voltage
·High transition frequency

APPLICATIONS

·Designed for use in Color TV chroma output circuits.

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

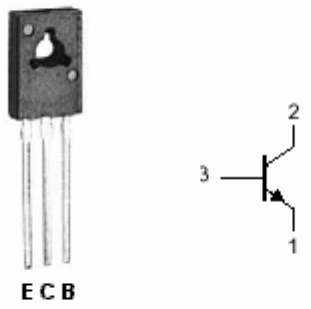

Fig.1 simplified outline (TO-126) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	300	V
V_{CEO}	Collector-emitter voltage	Open base	300	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		0.2	A
P_C	Collector power dissipation	T_a=25□	1.25	W
		T_C=25□	10	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=50mA; I_B=5mA			1.5	V
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=1mA; I_B=0	300			V
I_{CBO}	Collector cut-off current	V_{CB}=200V; I_E=0			0.1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			0.1	μA
h_{FE}	DC current gain	I_C=10mA ; V_{CE}=10V	40		250	
f_T	Transition frequency	I_C=10mA ; V_{CE}=30V	40			MHz
C_{re}	Feedback capacitance	I_E=0 ; V_{CB}=10V;f=1MHz			3.0	pF

◆ **h_{FE} Classifications**

N	M	L	K
40-80	60-120	100-200	160-250

PACKAGE OUTLINE

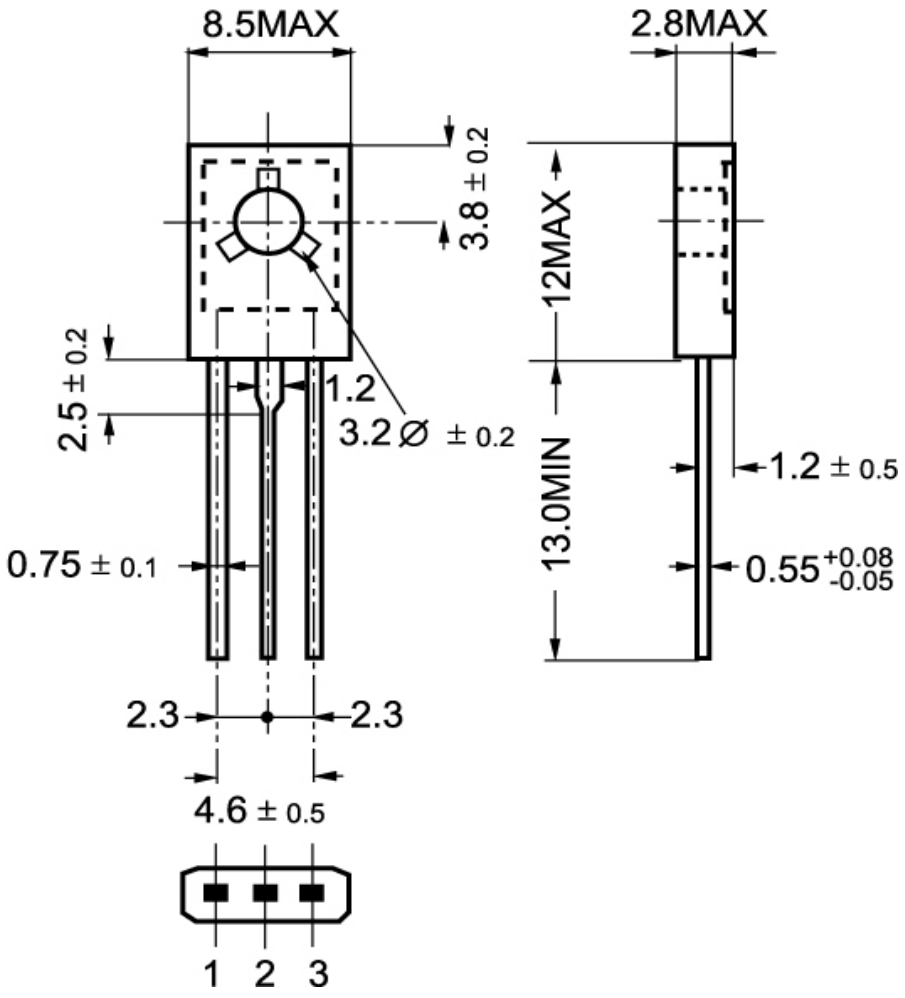

Fig.2 Outline dimensions